

MOS FIELD EFFECT TRANSISTOR

NP84N075CUE,NP84N075DUE,NP84N075EUE,NP84N075KUE

SWITCHING N-CHANNEL POWER MOS FET

75

±20

 ± 84

±260

1.8

200

175 -55 to +175

19 / 52 / 73

333 / 250 / 50

W

°C

Α

mJ

DESCRIPTION

These products are N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance

Drain to Source Voltage (Vgs = 0 V)

Gate to Source Voltage (VDS = 0 V)

Drain Current (DC) (Tc = 25°C) Note1

Total Power Dissipation (T_A = 25°C)

Total Power Dissipation (Tc = 25°C)

Drain Current (pulse) Note2

Channel Temperature

Storage Temperature

Single Avalanche Current Note3

Single Avalanche Energy Note3

 $R_{DS(on)} = 12.5 \text{ m}\Omega$ MAX. (Vgs = 10 V, ID = 42 A)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C)

• Low Ciss: Ciss = 5600 pF TYP.

ORDERING INFORMATION

PART NUMBER	PACKAGE
NP84N075CUE	TO-220AB
NP84N075DUE	TO-262
NP84N075EUE	TO-263 (MP-25ZJ)
NP84N075KUE	TO-263 (MP-25ZK)

(TO-220AB)



(TO-262)





Notes 1. Calculated constant current according to MAX. allowable channel temperature.

VDSS

VGSS

 $I_{D(DC)}$

ID(pulse)

 P_{T1}

 P_{T2}

Tch

Tstq

las

Eas

- **2.** PW \leq 10 μ s, Duty cycle \leq 1%
- 3. Starting Tch = 25°C, VDD = 35 V, Rg = 25 Ω , Vgs = 20 \rightarrow 0 V

THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	0.75	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W

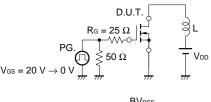
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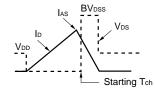


ELECTRICAL CHARACTERISTICS (TA = 25°C)

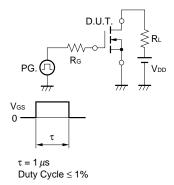
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V _{DS} = 75 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	Vgs = ±20 V, Vps = 0 V			±100	nA
Gate to Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.0	3.0	4.0	V
Forward Transfer Admittance	y fs	V _{DS} = 10 V, I _D = 42 A	21	43		S
Drain to Source On-state Resistance	RDS(on)	Vgs = 10 V, ID = 42 A		9.3	12.5	mΩ
Input Capacitance	Ciss	V _{DS} = 25 V		5600	8400	pF
Output Capacitance	Coss	V _G S = 0 V		530	800	pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		270	490	pF
Turn-on Delay Time	td(on)	V _{DD} = 38 V, I _D = 42 A		30	66	ns
Rise Time	t r	V _{GS} = 10 V		21	53	ns
Turn-off Delay Time	td(off)	$R_G = 0 \Omega$		72	150	ns
Fall Time	tf			12	30	ns
Total Gate Charge	Q _G	V _{DD} = 60 V		100	150	nC
Gate to Source Charge	Qgs	V _G S = 10 V		24		nC
Gate to Drain Charge	Q _{GD}	ID = 84 A		35		nC
Body Diode Forward Voltage	V _F (S-D)	IF = 84 A, Vgs = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 84 A, VGS = 0 V		70		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		200		nC

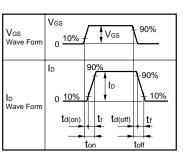
TEST CIRCUIT 1 AVALANCHE CAPABILITY





TEST CIRCUIT 2 SWITCHING TIME





TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C)



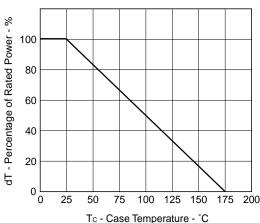


Figure 3. FORWARD BIAS SAFE OPERATING AREA

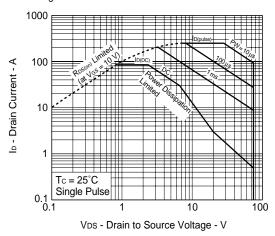


Figure 2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

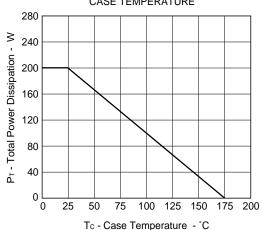
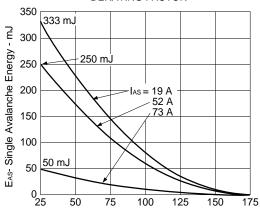
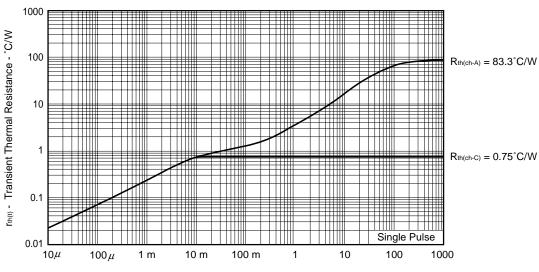


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR



Starting Tch - Starting Channel Temperature - °C





PW - Pulse Width - s

Figure 6. FORWARD TRANSFER CHARACTERISTICS

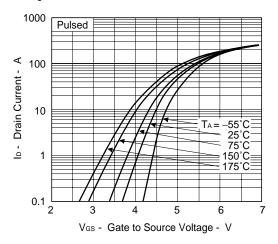


Figure8. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

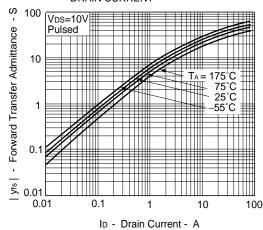


Figure 10. DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

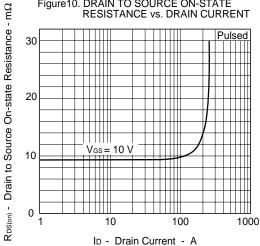
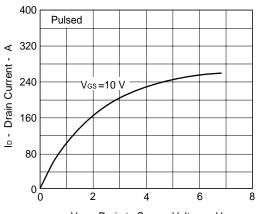


Figure 7. DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

Figure 9. DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

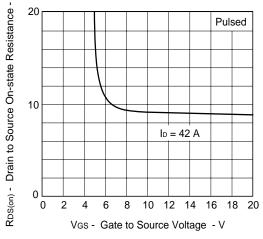
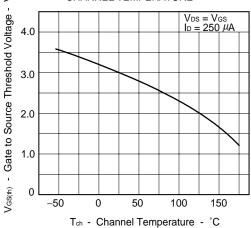


Figure 11. GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE





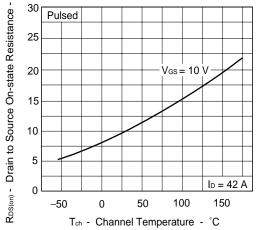
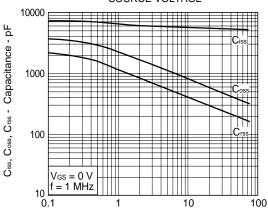


Figure14. CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



VDS - Drain to Source Voltage - V

Figure 16. REVERSE RECOVERY TIME vs. DRAIN CURRENT

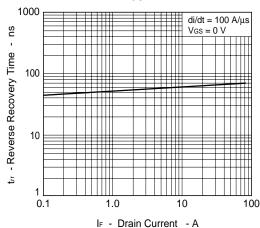
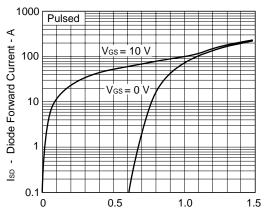


Figure 13. SOURCE TO DRAIN DIODE FORWARD VOLTAGE



VsD - Source to Drain Voltage - V

Figure 15. SWITCHING CHARACTERISTICS

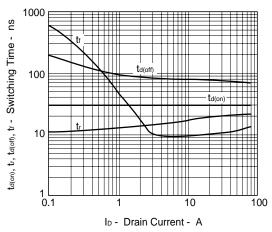
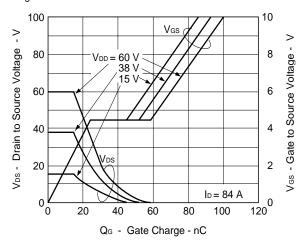
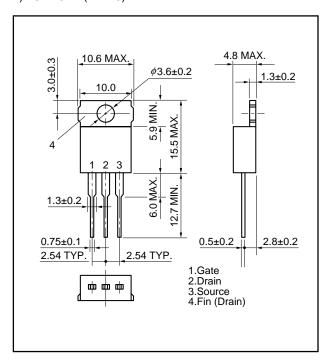


Figure 17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

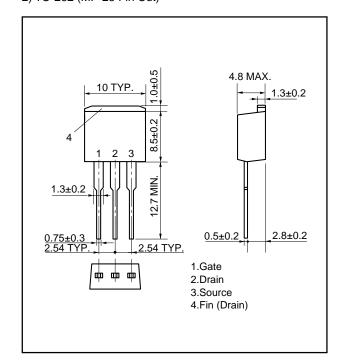


PACKAGE DRAWINGS (Unit: mm)

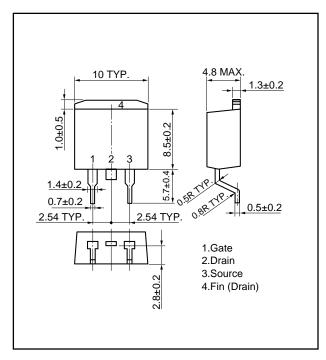
1) TO-220AB (MP-25)



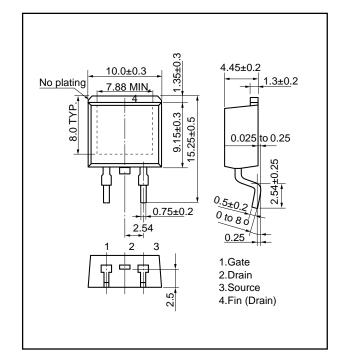
2) TO-262 (MP-25 Fin Cut)



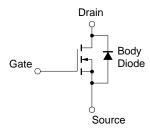
3) TO-263 (MP-25ZJ)



★ 4) TO-263 (MP-25ZK)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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